

TO-92 Plastic-Encapsulate Transistors

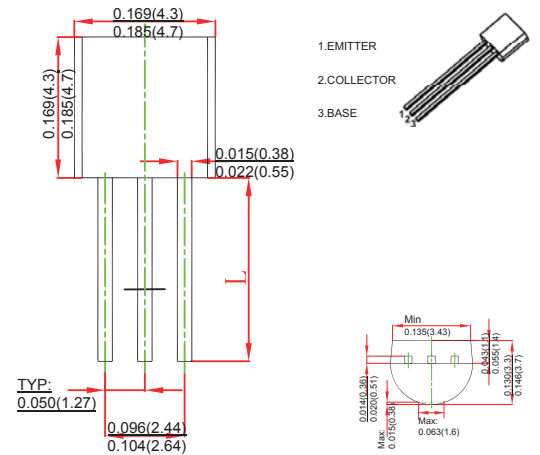
FEATURES

- General Purpose Switching Application
- Complementary to KTA1266.
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	60	V
V_{CE0}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.15	A
P_d	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	°C /W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS

$T_a = 25$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C = 0.1mA, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C = 5mA, I_B = 0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1mA, I_C = 0$	5			V
Collector cut-off current	I_{CB0}	$V_{CB} = 60V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 6V, I_C = 2mA$	70		700	
	$h_{FE(2)}$	$V_{CE} = 6V, I_C = 150mA$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100mA, I_B = 10mA$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100mA, I_B = 10mA$			1	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 1mA$	80			MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$			3.5	pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y	GR	BL
RANGE	70-140	120-240	200-400	300-700

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KTC3198	TO-92	Bulk	1000pcs/Bag
KTC3198-TA	TO-92	Tape	2000pcs/Box



RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

